



Average gate power dissipation ($T_j=125\text{ }^{\circ}\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25\text{ }^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS

ORDERING INFORMATION

<u>J</u>	<u>CT</u>	<u>8</u>	<u>12</u>	<u>C</u>
JieJie Microelectronics Co., Ltd.	SCRs			C:TO-220C
	8:V _{DRM} /V _{RRM} 1800V		I _{T(RMS)} :12A	

MARKING

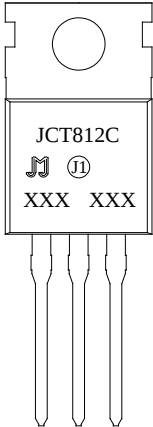
	XXX XXX Year _____ Month _____ Production Code
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FIG.1: Maximum power dissipation versus

PACKAGING INFORMATION

	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
	800	15	TO-220C	50	Tube

PACKAGE MECHANICAL DATA



